

L-Band Radar Transistor

The high power pulsed radar transistor device part number IB0810M100 is designed for L-Band radar systems operating over the instantaneous bandwidth of 870-990 MHz. While operating in class C mode at $V_{cc}=36V$, this common base device supplies a minimum of 100 watts of peak pulse power under the conditions of 300 μ s pulse width and 15% duty cycle. All devices are 100% screened for large signal RF parameters in a broadband RF test fixture with no external tuning. Excellent spectral stability into output mismatch over a broad input power range make it ideal for use in reliable high power solid state transmitters.



Silicon Bipolar

- Ultra-high f_T

Class C Operation

- High Efficiency

Common Base Configuration

- Single Power Supply

Gold Metal

- Maximum Reliability

Emitter Ballasting

- Optimum Thermal Distribution

Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

BeO Package

- Unmatched Thermal Reliability

RF Test Fixture

- Broadband
- Matched to 50 Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed
- Micro-strip structure on soft pc board with dielectric constant 10.5

TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

FREQ (MHz)	Pout (W)	Pin (W)	Ic (A)	IRL (dB)	Droop (dB)	Nc (%)	Delta Gain (dB)	VSWR	
								2:1	3:1
870	110	10	4.3	12	-0.12	71	0.21	S	P
930	116	10	4.5	14	-0.01	70		S	P
990	108	10	4.3	16	-0.10	69		S	P

Pulse Format = 300 μ s/15%

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	V_{CES}	--	75	V	--
BD	Emitter-Base Voltage	V_{EBO}	--	3	V	--
BD	Storage Temperature Range	T_{STG}	-65	+200	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.54	°C/W	$V_{CC}=36V$, Pulse format=300 μ s, 15%, $T_F=25\pm 5^\circ C$, $P_{IN}=10W$, $P_{out}=100W$ $N_C=50\%$
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	BV_{CES}	75	--	V	$I_C = 40mA$, $V_{BE} = 0V$, $T_F = 25\pm 5^\circ C$.
100%	Zero Base Voltage Collector Leakage Current	I_{CES}	--	10	mA	$V_{CE} = 30V$, $V_{BE} = 0V$, $T_F = 25\pm 5^\circ C$.
100%	DC Current Gain	H_{FE}	10	100	--	$V_{CE} = 5V$, $I_C = 0.5A$, $T_F = 25\pm 5^\circ C$.

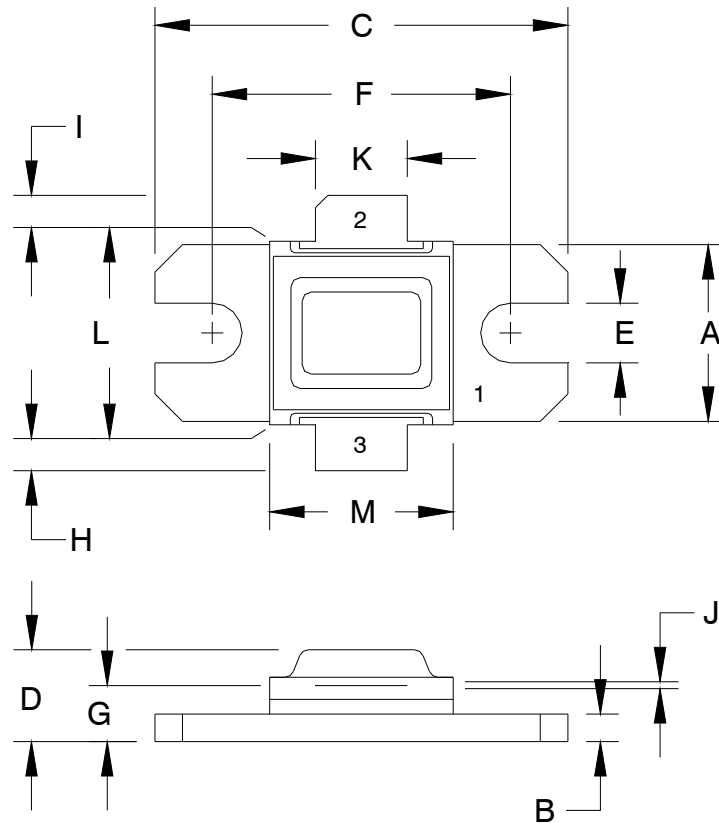
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	--	-10	dB	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$.
100%	Power Gain	G_p	10.0	--	dB	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$
100%	Collector Efficiency ($P_o/I_c/V_{CC}$)	N_c	50	--	%	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$.
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$.
100%	Stability into 2:1 VSWR	VSWR-S	3:1	--	--	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$. Rotate 2:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	Load Mismatch Tolerance	LMT	3:1	--	--	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$. Rotate 3:1 output VSWR through 360° phase. Survival.
100%	Output Power	Pout	100	--	dB	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$.
BD	Pulse Risetime	RT	--	100	ns	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$. Measure between 10% and 90% detected power points.
100%	Gain Flatness Versus Frequency	OPF	--	1.0	dB	$V_{CC}=36V$, $P_{IN}=10W$, Pulse = Note 2, $T_F=25\pm 5^\circ C$, $F=F1$.
100%	Output Power Flatness	OPC	0.01	0.5	dB	OPC measured with Pin increased by 0.5 dB at $F=F1$, $F2$, $F3$
Note 1	F1 = 870MHz, 930MHz, 990 MHz.					
Note 2	Pulse format = 300µs, 15%					
Note 3	T_F = Device flange temperature.					
Note 4	Screen 'BD' = parameter qualified By Design.					

RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
870	2.1-j1.8	2.0-j2.0
930	2.3-j1.7	2.1-j2.2
990	2.3-j1.6	2.2-j2.2
Impedance Definition		

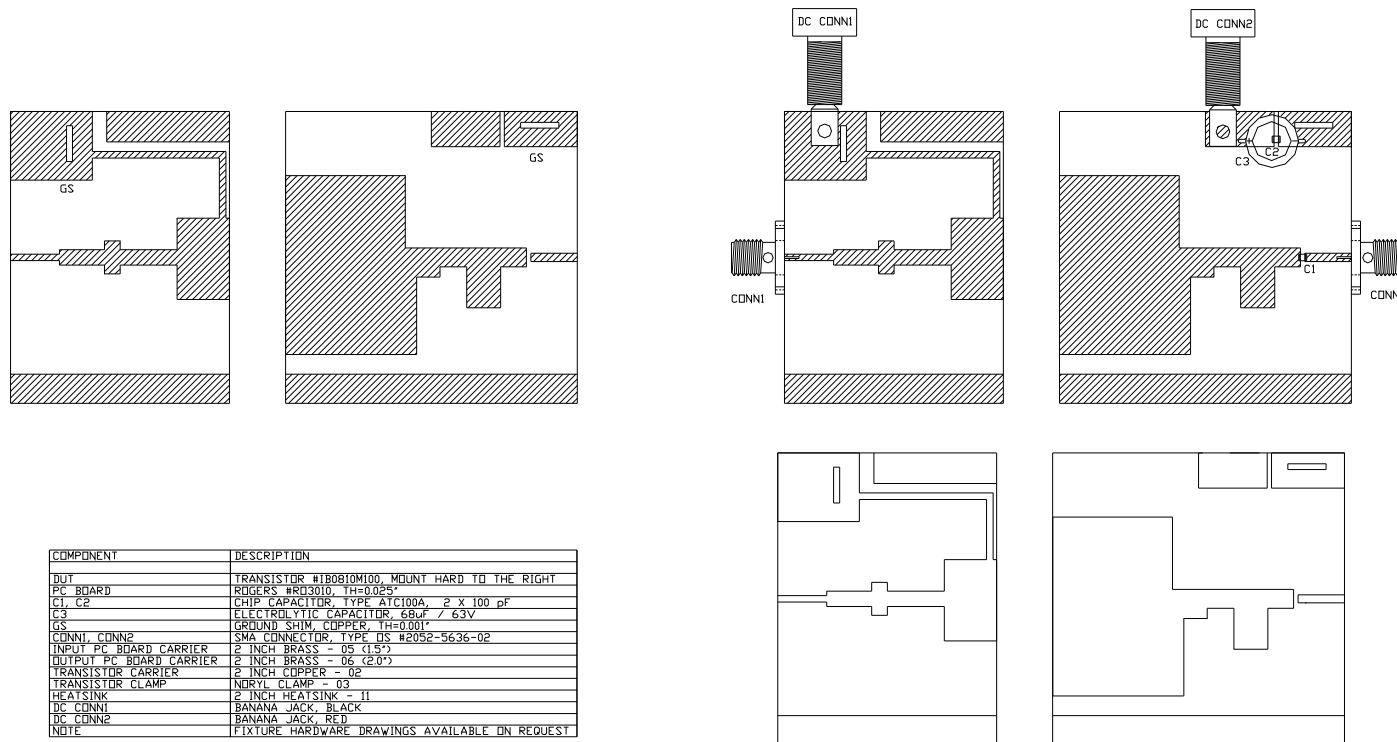
PACKAGE DIMENSIONAL OUTLINE DRAWING



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.380	0.390	9.65	9.91
B	0.058	0.062	1.47	1.57
C	0.895	0.905	22.73	22.99
D	0.195	0.205	4.95	5.21
E	0.125	0.135	3.18	3.43
F	0.645	0.655	16.38	16.64
G	0.112	0.132	2.84	3.35
H	0.080	0.120	2.03	3.05
I	0.080	0.120	2.03	3.05
J	0.003	0.005	0.08	0.13
K	0.195	0.205	4.95	5.21
L	0.395	0.405	10.03	10.29
M	0.395	0.405	10.03	10.29

PIN	
1	BASE
2	COLLECTOR
3	EMITTER

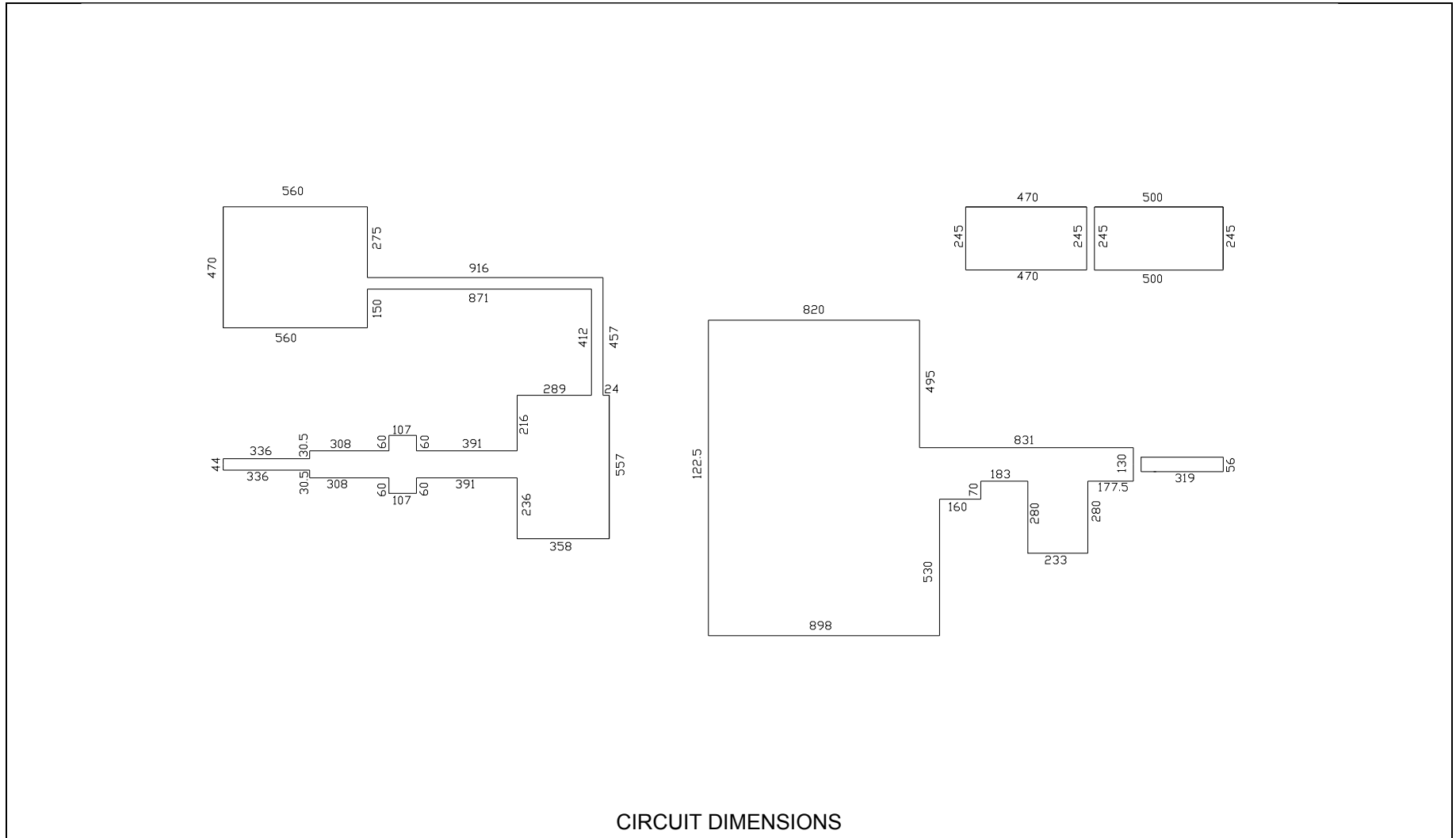
RF TEST FIXTURE



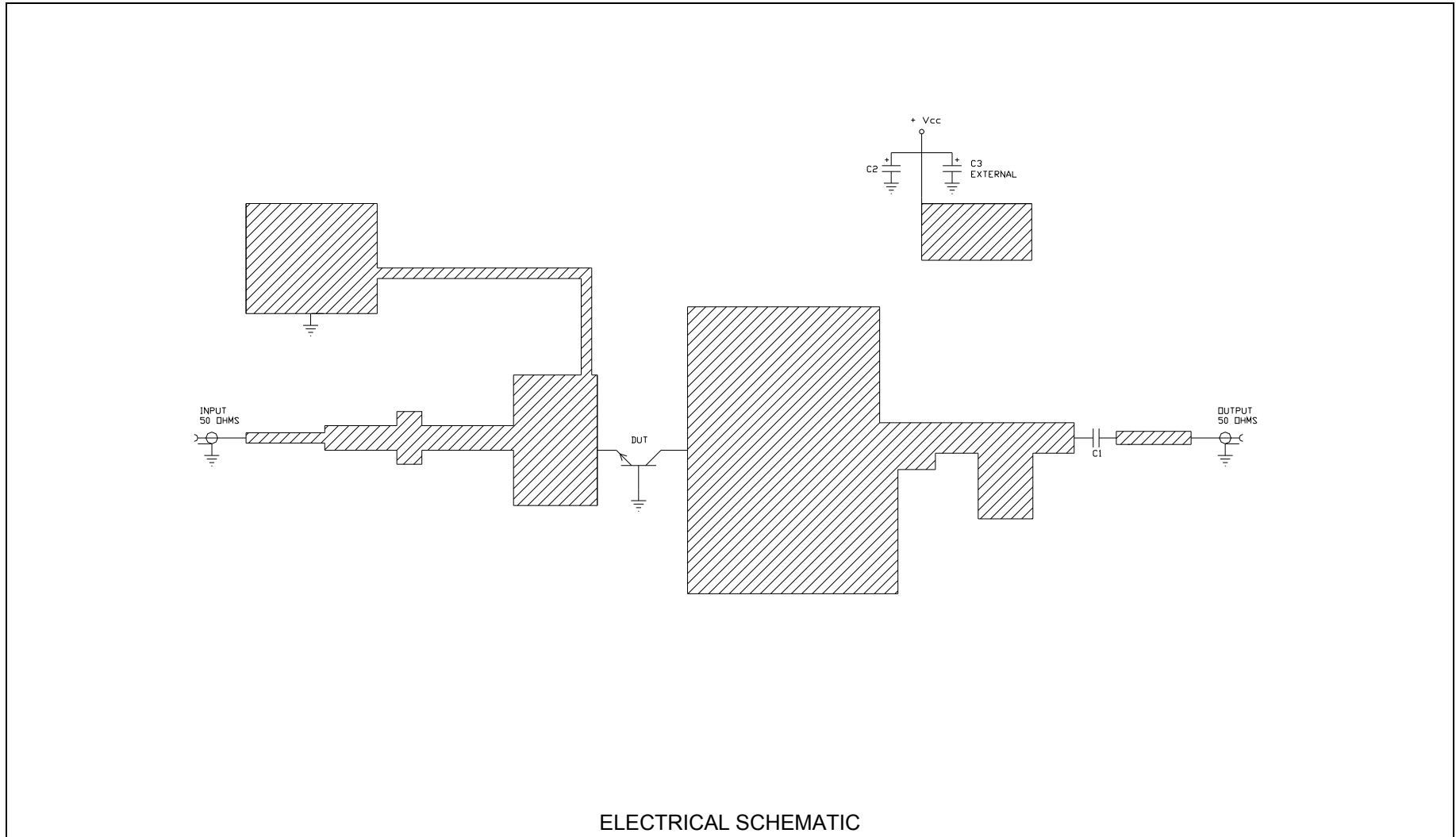
COMPONENT	DESCRIPTION
DUT	TRANSISTOR #IB0810M100, MOUNT HARD TO THE RIGHT
PC BOARD	ROGERS #R03010, TH=0.025"
C1, C2	CHIP CAPACITOR, TYPE ATC100A, 2 X 100 pF
C3	ELECTROLYTIC CAPACITOR, 68µF / 63V
GS	GROUND SHIM, COPPER, TH=0.001"
CONN1, CONN2	SMA CONNECTOR, TYPE DS #2052-5636-02
INPUT PC BOARD CARRIER	2 INCH BRASS - 05 (1.5")
OUTPUT PC BOARD CARRIER	2 INCH BRASS - 06 (2.0")
TRANSISTOR CARRIER	2 INCH COPPER - 02
TRANSISTOR CLAMP	NDRYL CLAMP - 03
HEATSINK	2 INCH HEATSINK - 11
DC CONN1	BANANA JACK BLACK
DC CONN2	BANANA JACK RED
NOTE	FIXTURE HARDWARE DRAWINGS AVAILABLE ON REQUEST

ASSEMBLY AND PARTS LIST

RF TEST FIXTURE



RF TEST FIXTURE



DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only and operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

DISCLAIMER

Integra Technologies Inc. reserves the right to make changes without further notice to any products herein. Integra Technologies Inc. makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Integra Technologies Inc. assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Integra Technologies Inc. products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Integra Technologies Inc. customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Integra Technologies Inc. for any damages resulting from such improper use or sale.
--